

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Slotted Optical Switch Type OPB817



Features

- .20" (5.08 mm) wide gap
- 24" minimum, 26 AWG wire leads
- Dust protection
- .86" (21.8 mm) deep slot

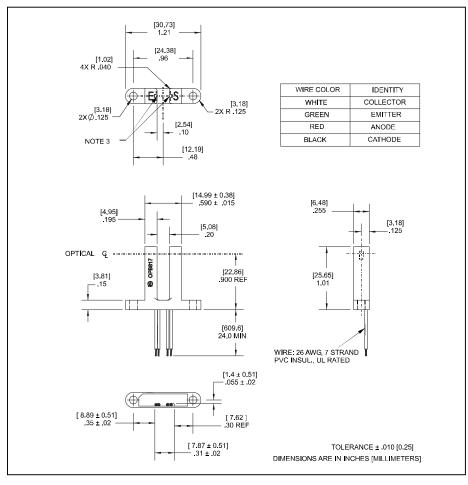
Description

The OPB817 consists of an infrared emitting diode and an NPN silicon phototransistor mounted in an opaque housing with clear windows for dust protection. The extended deep slot allows for a longer reach of the optical center line from the mounting plane, .90" (22.86 mm).

Internal apertures are $.010^{\circ}$ x 0.06° for the phototransistor "S side" and $.050^{\circ}$ x $.06^{\circ}$ for the LED "E side".

Custom electrical, wire or cabling is available. Contact your local representative or Optek for more information.

Visit our website at www.optekinc.com or email us at sensors@optekinc.com



Absolute Maximum Ratings (T_A = 25^o C unless otherwise noted)

Storage and Operating Temperature Range40 Input Diode	0° C to +80° C
Forward DC Current	50 mA
Peak Forward Current (1 µs pulse width, 300 pps)	3.0 A
Reverse DC Voltage	2.0 V
Power Dissipation	100 mW ⁽¹⁾
Output Phototransistor	
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5.0 V
Collector DC Current	
Power Dissipation	100 mW ⁽¹⁾

NOTES:

- (1) Derate linearly 1.67 mW/° C above 25° C.
- (2) All parameters tested using pulse technique.
- (3) Clear dust protection.

PRECAUTIONS: Exposure of the plastic body to chlorinated hydrocarbons and ketones such as thread lock and instant adhesive products will degrade the plastic body. Cleaning agents methanol and isopropanol are recommended. Spray or wipe do not submerge.

Type OPB817

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS	
Input Diode						
V _F	Forward Voltage		1.8	V	IF = 20 mA	
I _R	Reverse Current		100	μΑ	V _R = 2 V	
Phototransistor						
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30		V	$I_{C} = 1 \text{ mA}, I_{F} = 0, E_{e} = 0$	
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5.0		V	$I_E = 100 \mu\text{A}, I_F = 0, E_e = 0$	
ICEO	Collector-Emitter Leakage Current		100	nA	$V_{CE} = 10 \text{ V}, I_F = 0, E_e = 0$	
Coupled						
I _{C(ON)}	On-State Collector Current	1.0	10	mA	$V_{CE} = 5.0, I_F = 20 \text{ mA}$	
V _{CE(SAT)}	Collector-Emitter Saturation Voltage		0.40	V	$I_C = 100 \mu\text{A}, I_F = 20 \text{mA}$	